

KD502 Datasheet, Equivalent, Cross Reference Search

Type Designator: KD502

Material of Transistor: Si

Polarity: NPN

Maximum Collector Power Dissipation (P_c): 150 W

Maximum Collector-Base Voltage $|V_{cb}|$: 70 V

Maximum Collector-Emitter Voltage $|V_{ce}|$: 60 V

Maximum Emitter-Base Voltage $|V_{eb}|$: 5 V

Maximum Collector Current $|I_c \text{ max}|$: 20 A

Max. Operating Junction Temperature (T_j): 150 °C

Transition Frequency (f_t): 2 MHz

Forward Current Transfer Ratio (h_{FE}), MIN: 40

Noise Figure, dB: -

Package: TO3